

opening). The first insulating film 104 is formed to a thickness of about 5000 angstroms by a known oxidation technique. A known photolithography/etching technique is used to open the first insulating film 104 in a region forming a D well, and a first insulating film 104b is formed in about 200 angstroms by the known oxidation technique.

A1
Replace the paragraph beginning on page 9, line 9 with the following paragraph:

First, a first diffusion layer (well) 203 of the second conductivity type is formed in a portion on a semiconductor substrate 201 of the first conductivity type. Next, a first insulating film 204 is formed on the semiconductor substrate 201 of the first conductivity type. A portion of the first insulating film 204 above the first diffusion layer 203 of the second conductivity type is opened, and a first opening 204a is formed. (Fig. 2(A)) A second diffusion layer (D well) 205 of the first conductivity type is formed in a portion in the first diffusion layer 203 of the second conductivity type via the first opening 204a. (Fig. 2(A))

A2
Replace the paragraph beginning on page 11, line 6 with the following paragraph:

Subsequently, a fifth diffusion layer 211 in first diffusion layer 203, and a sixth diffusion layer 212 of the first conductivity type is formed in a portion in the second diffusion layer 205 of the first conductivity type and connected to the second diffusion